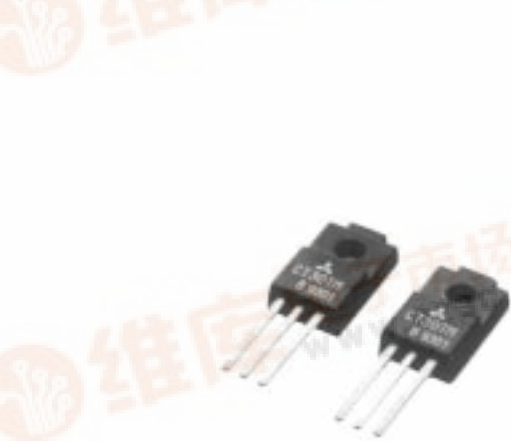


MITSUBISHI INSULATED GATE BIPOLAR TRANSISTOR

CT30TM-8

STROBE FLASHER USE

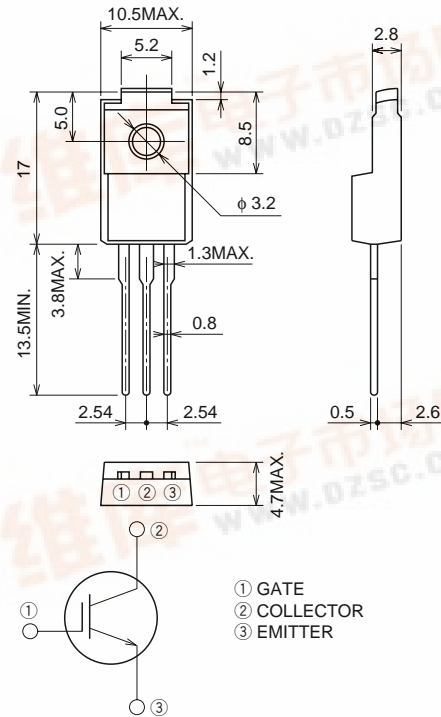
CT30TM-8



- VCES 400V
- ICM 180A

OUTLINE DRAWING

Dimensions in mm



TO-220F

APPLICATION

Strobe Flasher.

MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
VCES	Collector-emitter voltage	VGE = 0V	400	V
VGES	Gate-emitter voltage	VCE = 0V, See notice 4	±30	V
VGEM	Peak gate-emitter voltage	VCE = 0V, tw = 0.5s	±40	V
ICM	Collector current (Pulsed)	See figure 1	180	A
Tj	Junction temperature		-40 ~ +150	°C
Tstg	Storage temperature		-40 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Tj = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)CES	Collector-emitter breakdown voltage	IC = 1mA, VGE = 0V	450	—	—	V
ICES	Collector-emitter leakage current	VCE = 400V, VGE = 0V	—	—	10	μA
IGES	Gate-emitter leakage current	VGE = ±40V, VCE = 0V	—	—	±0.1	μA
VGE(th)	Gate-emitter threshold voltage	VCE = 10V, IC = 1mA	—	—	7.0	V

PERFORMANCE CURVES

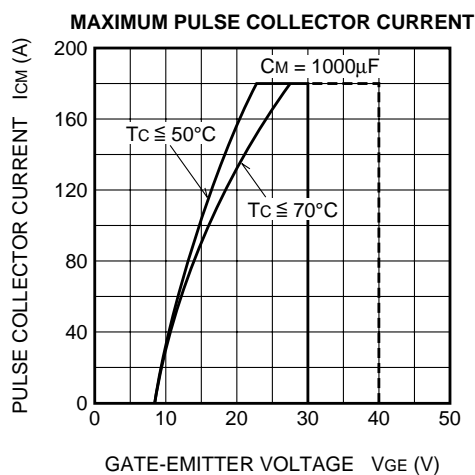


Figure 1

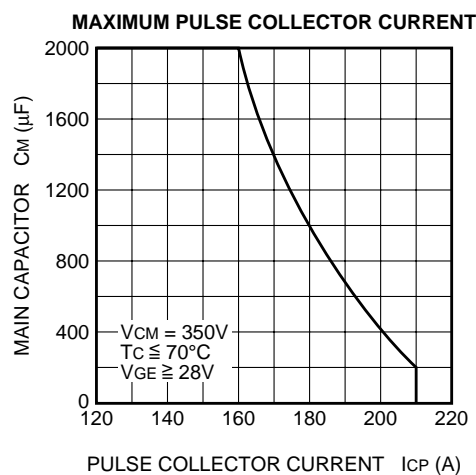
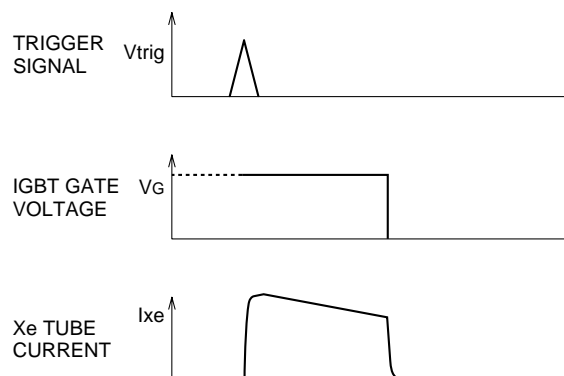
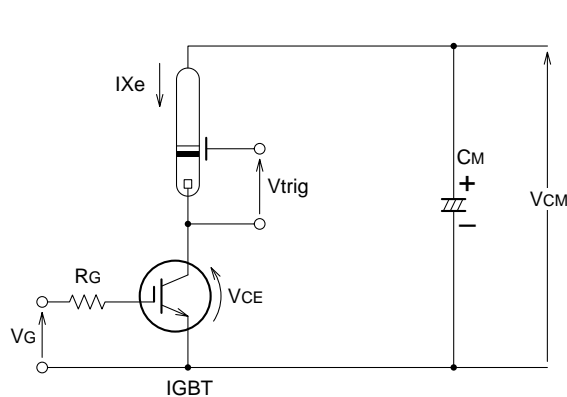


Figure 2

APPLICATION EXAMPLE



RECOMMEND CONDITION MAXIMUM CONDITION

$V_{CM} = 330V$	360V
$I_P = 160A$	180A
$C_M = 800\mu F$	1000 μF
$V_{GE} = 28V$	

- Notice 1. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current.
And reverse gate current during turn-off must be kept less than 1A.
(In general, it is satisfied if $R_G \geq 30\Omega$)
- Notice 2. IGBT has MOS structure and its gate is insulated by thin silicon oxide.
So please handle carefully not to suffer from electrostatic charge.
- Notice 3. The operation life should be endured 5,000 shots under the charge current ($I_{xe} \leq 180A$: full luminescence condition) of main condenser ($C_M=1000\mu F$).
Repetition period under full luminescence condition is over 3 seconds.
- Notice 4. Total operation hours must be applied within 5,000 hours.